PATENT COOPERATION TREATY

PCT

INTERNATIONAL SEARCH REPORT

(PCT Article 18 and Rules 43 and 44)

Applicant's or agent's file reference OPP031614KR	FOR FURTHER ACTION	see Form PCT/ISA/220 as well as, where applicable, item 5 below.
International application No. PCT/KR 2005/000380	(Earliest) Priority Date (day/month/year 9 February 2004 (09.02.2004	International filing date (day/month/year) 7 February 2005 (07.02.2005)
Applicant	SAMSUNG ELECTRONICS C	O., LTD.
This international search report has been according to Article 18. A copy is being	n prepared by this International Searching transmitted to the International Bureau.	Authority and is transmitted to the applicant
This international search report consists	of a total of 4 sheets.	
	a copy of each prior art document cited i	n this report.
1. Basis of the report a. With regard to the language, the language in which it was filed, u	international search was carried out on the nless otherwise indicated under this item.	ne basis of the international application in the
	al search was carried out on the basis of a y (Rule 23.1(b)).	translation of the international application furnished
b. With regard to any nucleoti	de and/or amino acid sequence disclose	ed in the international application, see continuation of this first sheet.
2. Certain claims were fou	nd unsearchable (see continuation of the	is first sheet)
3. Unity of invention is lac	king (see continuation of this first sheet)	
4. With regard to the title,		
the text is approved as su	bmitted by the applicant.	
the text has been establish	hed by this Authority to read as follows:	
		•
	·	
5. With regard to the abstract,		
	ubmitted by the applicant.	A A STATE OF THE S
the text has been established. The applicant may comments to this Author	y, within one month from the date of mail	authority as it appears in the continuation of this first ling of this international search report, submit
6. With regard to the drawings,		
	gs to be published with the abstract is Fig	gure No. 2
as suggested by the appl	licant.	
as selected by this Author	ority, because the applicant failed to sugg	gest a figure.
as selected by this Author	ority, because this figure better characteri	izes the invention.
b. \square none of the figures is to be	e published with the abstract.	

INTERNATIONAL SEARCH REPORT

International application No. PCT/KR 2005/000380

Continuation of first sheet

1. With regard to any nucleotide and/or amino acid sequence disclosed in the international application and necessary to the claimed invention, the international search was carried out on the basis of:

Continuation No. IV:

Text of the abstract

(Continuation of item 5 of the first sheet)

The present invention provides a thin film transistor comprising: a substrate (110); a gate electrode (124) formed on the substrate; a gate insulating layer (140) covering the substrate and the gate electrode; a source electrode and a drain electrode (173,175) formed on the gate insulating layer; a semiconductor layer (150) formed on the gate insulating layer, the source electrode and the drain electrode; and a passivation layer (180) covering the semiconductor layer, the source electrode, the drain electrode and the gate insulating layer, wherein at least one of the gate insulating layer and the passivation layer is made of Parylene.

INTERNATIONAL SEARCH REPORT

International application No. PCT/KR 2005/000380

IPC ⁷ : H01	FICATION OF SUBJECT MATTER L 29/786, H01L 27/12, G02F 1/1368 International Patent Classification (IPC) or to both nat	tional classification and IPC			
B. FIELDS	SEARCHED				
Minimum doo IPC ⁷ : H01	cumentation searched (classification system followed l L, G02F	by classification symbols)			
Documentation	on searched other than minimum documentation to the	extent that such documents are included	d in the fields searched		
	ta base consulted during the international search (name VPI, PAJ, TXT, Inspec, XPIEE, XPESP,	·	arch terms used)		
C. DOCUM	MENTS CONSIDERED TO BE RELEVANT				
Category*	Citation of document, with indication, where ap	propriate, of the relevant passages	Relevant to claim No.		
×	DE 19712233 A1 (LG ELECTRONICS (30.10.1997) page 5, lines 7-11; page 11, line 61 - p 10A-11F.	7,8,9			
×	US 6211928 B1 (OH et al) 3 April 20 abstarct; figures 8A-8J and the associ	7			
P,X		ESE C. et al. Organic thin fim transistors. Materials Today. ptember 2004, Vol. 7, No. 9, pages 20-27 ction "device design and fabrication".			
Further	documents are listed in the continuation of Box C.	See patent family annex.	-		
* Special of "A" document to be of parties as filing date "L" document cited to special remains "O" document means "P" document	categories of cited documents: It defining the general state of the art which is not considered particular relevance opposition or patent but published on or after the internation	"T" later document published after to priority date and not in conflict to understand the principle or the al "X" document of particular relevation cannot be considered novel or cat an inventive step when the document of particular relevation cannot be considered to involve document is combined with documents, such combination	with the application but cited cory underlying the invention mee; the claimed invention ment be considered to involve ment is taken alone mee; the claimed invention e an inventive step when the one or more other such being obvious to a person		
Date of the a	actual completion of the international search 24 May 2005 (24.05.2005)	Date of mailing of the international se 8 June 2005 (08.	•		
	nailing address of the ISA/AT Austrian Patent Office esdner Straße 87, A-1200 Vienna	Authorized officer HARASEK S.			
Facsimile No. +43 / 1 / 534 24 / 535 Telephone No. +43 / 1 / 534 24 / 574					

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No. PCT/KR 2005/000380

Patent document cited in search report			Publication date	Patent family member(s)		Publication date	
	A					none	
DE	A1	19712233	1997-10-30	US	B1	6211928	2001-04-03
				JP	A	10041519	1998-02-13
				GB	A	2311653	1997-10-01
			•	US	A	6100954	2000-08-08
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				GB	A	2316793	1998-03-04
				US	B1	6188452	2001-02-13